SGS-THOMSON MICROELECTRONICS

TMBAT49

SMALL SIGNAL SCHOTTKY DIODE



DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching.

This device has integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
VRRM	Repetitive Peak Reverse Voltage	80	V	
١ _F	Forward Continuous Current T ₁ = 70°C		500	mA
IFRM	$\begin{array}{l} \mbox{Repetitive Peak Forward Current} & t_p = 1s \\ \delta \leq 0.5 \end{array}$		3	A
IFSM	Surge non Repetitive Forward Current	non Repetitive Forward Current t _p = 10ms		A
T _{stg} T _i	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	0° ℃
TL	Maximum Temperature for Soldering during 15 s		260	°C

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-l)	Junction-leads	110	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Test Conditions	Min.	Тур.	Max.	Unit
I _R *	$T_j = 25^{\circ}C$	V _R = 80V			200	μA
V _F *	$T_j = 25^{\circ}C$	$I_F = 10 \text{mA}$			0.32	V
	$T_j = 25^{\circ}C$	I _F = 100mA			0.42	
	$T_j = 25^{\circ}C$	I _F = 1A			1	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	$T_j = 25^{\circ}C$	f = 1MHz	$V_{R} = 0V$		120		рF
			V _R = 5V		35		

* Pulse test : $t_p \le 300 \mu s \quad \delta < 2\%$.

TMBAT49



Fig.1 - Forward current versus forward voltage at low level (typical values).



Fig.3 - Aeverse current versus junction temperature.



Fig.2 - Forward current versus forward voltage at high level (typical values).









Fig.5 - Capacitance C versus reverse applied voltage V_R (typical values).



Fig.6 - Surge non repetitive forward current for a rectangular pulse with t \leqslant 10 ms.





